

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

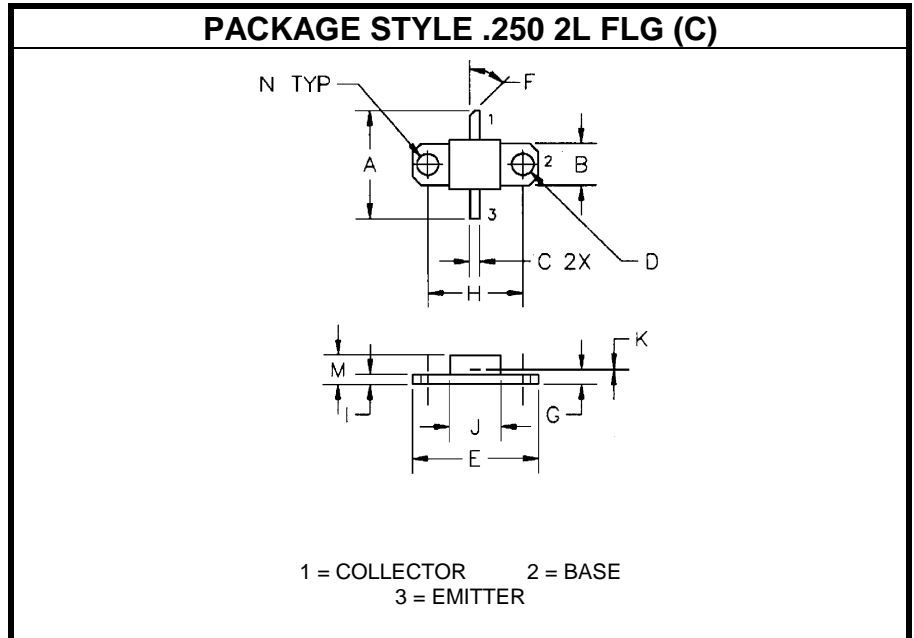
The **ASI MRAL2023-6** is a Common Base Device Designed for class C Amplifier Applications in L-Band FM Microwave Links.

FEATURES INCLUDE:

- Gold Metallization
- Emitter Ballasting
- Input Matching

MAXIMUM RATINGS

I_C	1.25 A
V_{CES}	40 V
P_{DISS}	21 W @ $T_C = 25\text{ }^{\circ}\text{C}$
T_J	-65 $^{\circ}\text{C}$ to +200 $^{\circ}\text{C}$
T_{STG}	-65 $^{\circ}\text{C}$ to +150 $^{\circ}\text{C}$
θ_{JC}	8.0 $^{\circ}\text{C/W}$



CHARACTERISTICS $T_C = 25\text{ }^{\circ}\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 50\text{ mA}$	40			V
BV_{EBO}	$I_E = 1.0\text{ mA}$	3.5			V
I_{CBO}	$V_{CB} = 22\text{ V}$			1.25	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 500\text{ mA}$	10		90	---
C_{OB}	$V_{CB} = 22\text{ V}$ $f = 1.0\text{ MHz}$			10	pF
P_G	$V_{CE} = 22\text{ V}$ $P_{OUT} = 6.0\text{ W}$ $f = 2000\text{ to }2300\text{ MHz}$	6.8			dB
η_C		40			%